

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVU100** is Designed for Television Band IV & V Applications up to 860 MHz.

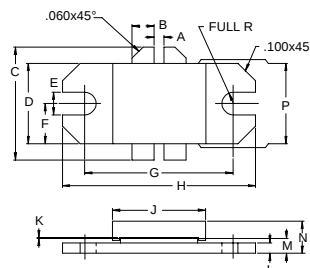
FEATURES:

- Common Emitter
- $P_G = 8.5$ dB at 100 W/860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.0 $^\circ\text{C/W}$

PACKAGE STYLE .450 BAL FLG(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.055 / 1.40
B	.120 / 3.05	.130 / 3.30
C		.785 / 19.94
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F		.230 / 5.84
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N		.195 / 4.95
P	.445 / 11.30	.455 / 11.56

ORDER CODE: ASI10651

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
P_{GE}	$V_{CE} = 25$ V $I_{CQ} = 2 \times 100$ mA $f = 860$ MHz $P_{OUT} = 100$ W	8.5			dB